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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 15x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302r8t6tr

List of tables

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F302x6/8 microcontrollers.

This datasheet should be read in conjunction with the STM32F302xB/C/D/E and STM32F302x6/8 advanced ARM®-based 32-bit MCUs reference manual (RM0365). The reference manual is available from the STMicroelectronics website *www.st.com*.

For information on the ARM® Cortex®-M4 core, please refer to the Cortex®-M4 Technical Reference Manual, available from ARM website www.arm.com.

2 Description

The STM32F302x6/8 family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core operating at a frequency of up to 72 MHz and embedding a floating point unit (FPU). The family incorporates high-speed embedded memories (up to 64 Kbytes of Flash memory, 16 Kbytes of SRAM), and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The devices offer a fast 12-bit ADC (5 Msps), three comparators, an operational amplifier, up to 18 capacitive sensing channels, one DAC channel, a low-power RTC, one general-purpose 32-bit timer, one timer dedicated to motor control, and up to three general-purpose 16-bit timers, and one timer to drive the DAC. They also feature standard and advanced communication interfaces: three I^2Cs, up to three USARTs, up to two SPIs with multiplexed full-duplex I2S, a USB FS device, a CAN, and an infrared transmitter.

The STM32F302x6/8 family operates in the –40 to +85°C and –40 to +105°C temperature ranges from at a 2.0 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F302x6/8 family offers devices in 32-, 48-, 49- and 64-pin packages.

The set of included peripherals changes with the device chosen.

Figure 2. Clock tree

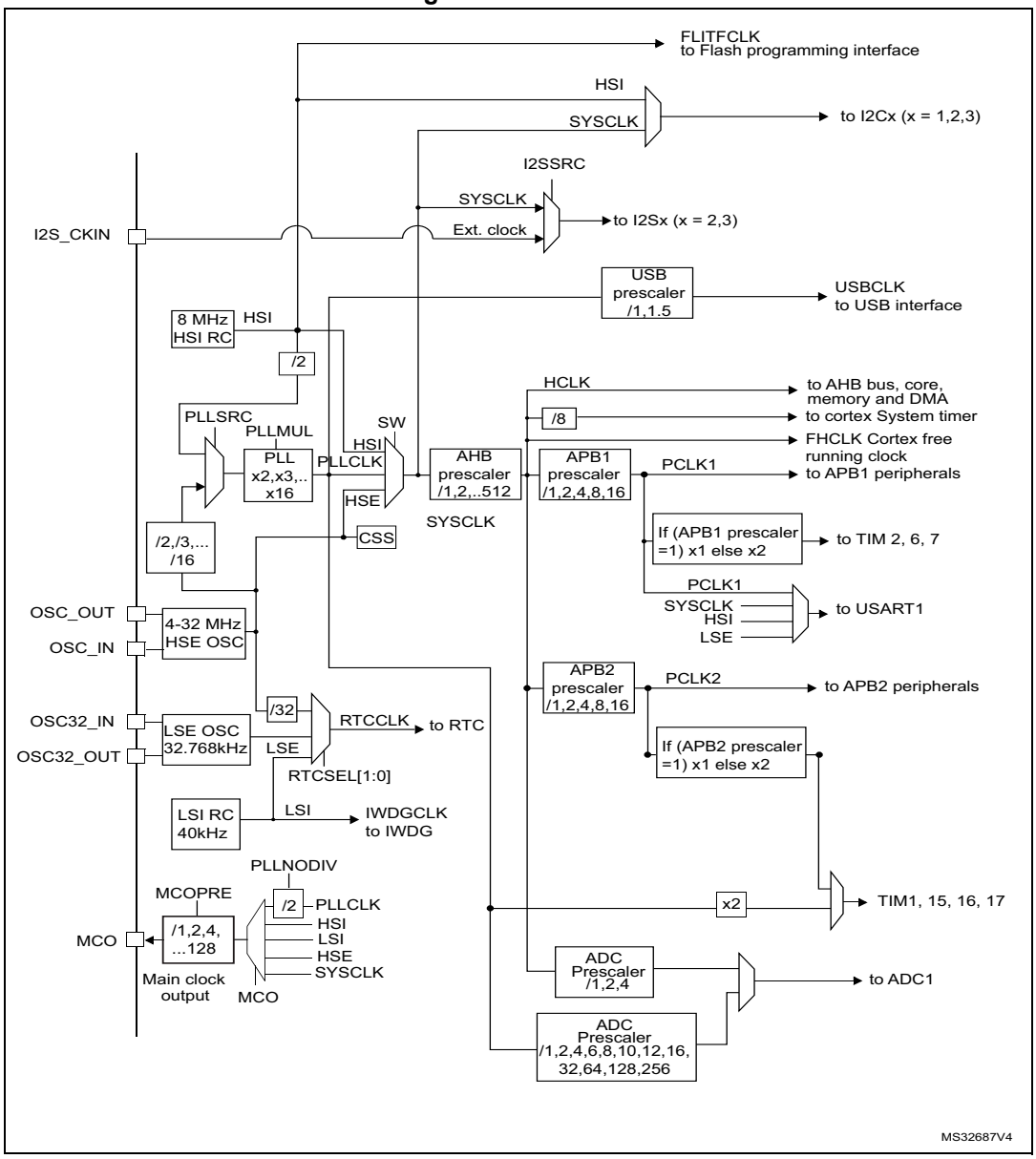


Table 12. STM32F302x6/8 pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
-	-	-	51	PC10	I/O	FT	-	EVENTOUT, SPI3_SCK/I2S3_CK, USART3_TX	-
-	-	-	52	PC11	I/O	FT	-	EVENTOUT, SPI3_MISO/I2S3ext_SD, USART3_RX	-
-	-	-	53	PC12	I/O	FT	-	EVENTOUT, SPI3_MOSI/I2S3_SD, USART3_CK	-
-	-	-	54	PD2	I/O	FT	-	EVENTOUT	-
26	A3	39	55	PB3	I/O	FT	-	JTDO-TRACESWO, TIM2_CH2, TSC_G5_IO1, SPI3_SCK/I2S3_CK, USART2_TX, EVENTOUT	-
27	A4	40	56	PB4	I/O	FT	-	JTRST, TIM16_CH1, TSC_G5_IO2, SPI3_MISO/I2S3ext_SD, USART2_RX, TIM17_BKIN, EVENTOUT	-
28	B4	41	57	PB5	I/O	FT	-	TIM16_BKIN, I2C1_SMBAI, SPI3_MOSI/I2S3_SD, USART2_CK, I2C3_SDA, TIM17_CH1, EVENTOUT	-
29	C4	42	58	PB6	I/O	FTf	-	TIM16_CH1N, TSC_G5_IO3, I2C1_SCL, USART1_TX, EVENTOUT	-
30	D4	43	59	PB7	I/O	FTf	-	TIM17_CH1N, TSC_G5_IO4, I2C1_SDA, USART1_RX, EVENTOUT	-

Table 12. STM32F302x6/8 pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
31	A5	44	60	BOOT0	I	B	-	Boot memory selection	
-	B5	45	61	PB8	I/O	FTf	-	TIM16_CH1, TSC_SYNC, I2C1_SCL, USART3_RX, CAN_RX, TIM1_BKIN, EVENTOUT	-
-	C5	46	62	PB9	I/O	FTf	-	TIM17_CH1, I2C1_SDA, IR-OUT, USART3_TX, COMP2_OUT, CAN_TX, EVENTOUT	-
32	D3	47	63	VSS_1	S	-	-	Digital ground	
"1"	B7	48	64	VDD_1	S	-	-	Digital power supply	

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch sinks only a limited amount of current (3 mA), the use of GPIO PC13 to PC15 in output mode is limited:

   - The speed should not exceed 2 MHz with a maximum load of 30 pF

   - These GPIOs must not be used as current sources (e.g. to drive an LED).

   After the first backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the Backup registers which is not reset by the main reset. For details on how to manage these GPIOs, refer to the Battery backup domain and BKP register description sections in the RM0365 reference manual.

2. Fast ADC channel.

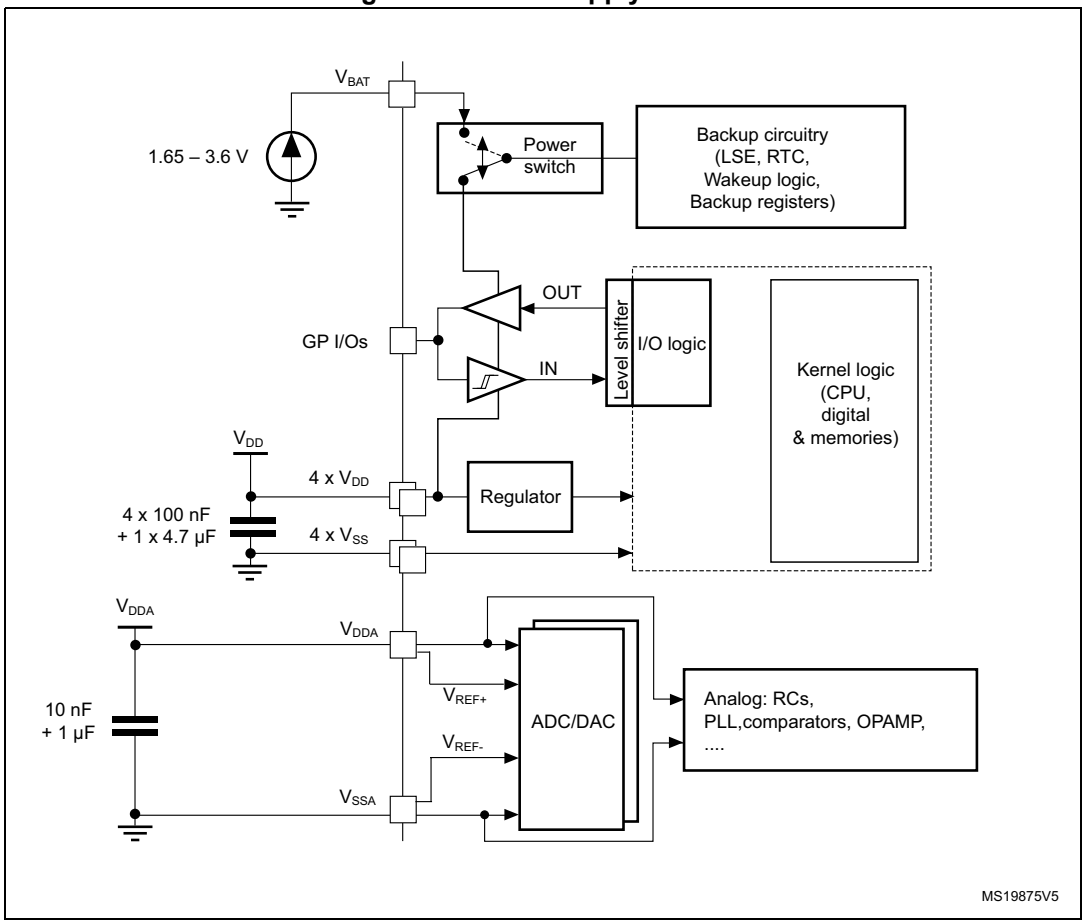
3. These GPIOs offer a reduced touch sensing sensitivity. It is thus recommended to use them as sampling capacitor I/O.

Table 15. Alternate functions for Port C

Port & pin name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
	SYS_AF	TIM2/TIM15/ TIM16/TIM17/ EVENT	I2C3/TIM1/TIM2 /TIM15	I2C3/TIM15/ TSC	I2C1/I2C2/TIM1/ TIM16/TIM17	SPI2/I2S2/ SPI3/I2S3 Infrared	SPI2/I2S2/SPI3/ I2S3/TIM1/ Infrared	USART1/ USART2/ USART3/CAN/ GPCOMP6
PC0	-	EVENTOUT	TIM1_CH1	-	-	-	-	-
PC1	-	EVENTOUT	TIM1_CH2	-	-	-	-	-
PC2	-	EVENTOUT	TIM1_CH3	-	-	-	-	-
PC3	-	EVENTOUT	TIM1_CH4	-	-	-	TIM1_BKIN2	-
PC4	-	EVENTOUT	TIM1_ETR	-	-	-	-	USART1_TX
PC5	-	EVENTOUT	TIM15_BKIN	TSC_G3_IO1	-	-	-	USART1_RX
PC6	-	EVENTOUT	-	-	-	-	I2S2_MCK	COMP6_OUT
PC7	-	EVENTOUT	-	-	-	-	I2S3_MCK	-
PC8	-	EVENTOUT	-	-	-	-	-	-
PC9	-	EVENTOUT	-	I2C3_SDA	-	I2SCKIN	-	-
PC10	-	EVENTOUT	-	-	-	-	SPI3_SCK/ I2S3_CK	USART3_TX
PC11	-	EVENTOUT	-	-	-	-	SPI3_MISO/ I2S3ext_SD	USART3_RX
PC12	-	EVENTOUT	-	-	-	-	SPI3_MOSI/ I2S3_SD	USART3_CK
PC13	-	-	-	-	TIM1_CH1N	-	-	-
PC14	-	-	-	-	-	-	-	-
PC15	-	-	-	-	-	-	-	-

6.1.6 Power supply scheme

Figure 11. Power supply scheme



Caution: Each power supply pair (for example V_{DD}/V_{SS}, V_{DDA}/V_{SSA}) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

Table 25. Programmable voltage detector characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{PVD0}	PVD threshold 0	Rising edge	2.1	2.18	2.26	V
		Falling edge	2	2.08	2.16	
V_{PVD1}	PVD threshold 1	Rising edge	2.19	2.28	2.37	
		Falling edge	2.09	2.18	2.27	
V_{PVD2}	PVD threshold 2	Rising edge	2.28	2.38	2.48	
		Falling edge	2.18	2.28	2.38	
V_{PVD3}	PVD threshold 3	Rising edge	2.38	2.48	2.58	
		Falling edge	2.28	2.38	2.48	
V_{PVD4}	PVD threshold 4	Rising edge	2.47	2.58	2.69	
		Falling edge	2.37	2.48	2.59	
V_{PVD5}	PVD threshold 5	Rising edge	2.57	2.68	2.79	
		Falling edge	2.47	2.58	2.69	
V_{PVD6}	PVD threshold 6	Rising edge	2.66	2.78	2.9	
		Falling edge	2.56	2.68	2.8	
V_{PVD7}	PVD threshold 7	Rising edge	2.76	2.88	3	
		Falling edge	2.66	2.78	2.9	
$V_{PVDhyst}$(2)	PVD hysteresis	-	-	100	-	mV
IDD(PVD)	PVD current consumption	-	-	0.15	0.26	µA

1. Guaranteed by characterization results.
2. Guaranteed by design.

Table 28. Typical and maximum current consumption from VDD supply at VDD = 3.6V (continued)

Symbol	Parameter	Conditions	f_{HCLK}	All peripherals enabled				All peripherals disabled				Unit
				Typ	Max @ T_A(1)			Typ	Max @ T_A(1)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DD}	Supply current in Run mode, executing from RAM	External clock (HSE bypass)	72 MHz	45.8	49.1(2)	50.1	51.4(2)	25.1	27.3(2)	28.0	28.6(2)	mA
			64 MHz	40.8	43.6	44.9	46.9	22.3	24.1	25.0	25.5	
			48 MHz	30.2	32.9	33.5	34.8	17.0	18.7	19.1	19.6	
			32 MHz	20.5	23.1	24.1	25.4	11.1	12.2	13.2	13.3	
			24 MHz	15.4	17.1	18.3	19.5	8.5	9.7	10.1	10.2	
			8 MHz	5.0	5.9	6.3	6.9	3.1	3.7	4.1	4.7	
			1 MHz	0.8	1.1	1.9	2.6	0.5	0.8	1.2	1.4	
		Internal clock (HSI)	64 MHz	37.3	41.1	41.8	43.3	22.0	23.8	24.4	24.9	
			48 MHz	28.0	31.1	31.6	33.2	16.4	18.0	18.3	18.6	
			32 MHz	18.8	21.3	22.1	23.1	10.9	11.9	12.8	13.1	
			24 MHz	14.2	15.9	16.8	17.9	5.5	6.4	6.7	7.3	
			8 MHz	4.8	5.1	6.0	6.5	2.9	3.5	4.1	4.2	
I_{DD}	Supply current in Sleep mode, executing from Flash or RAM	External clock (HSE bypass)	72 MHz	30.0	32.8(2)	33.1	34.1(2)	5.9	6.8(2)	6.9	7.4(2)	
			64 MHz	26.7	29.2	29.6	30.5	5.3	5.9	6.2	6.7	
			48 MHz	16.7	18.5	19.0	19.7	3.6	4.5	4.5	5.3	
			32 MHz	13.3	14.9	15.3	15.4	2.9	3.7	3.8	4.3	
			24 MHz	10.2	11.4	12.0	12.3	2.2	2.7	2.9	3.2	
			8 MHz	3.6	4.4	4.8	5.3	0.9	1.2	1.5	2.1	
			1 MHz	0.5	0.8	1.1	1.3	0.1	0.4	0.8	0.8	
		Internal clock (HSI)	64 MHz	23.2	25.3	25.6	26.2	5.0	5.7	6.1	6.2	mA
			48 MHz	17.5	19.2	19.4	19.9	3.9	4.7	4.8	5.3	
			32 MHz	11.7	12.9	13.2	13.3	2.6	3.4	3.6	4.2	
			24 MHz	8.9	10.2	10.6	10.8	1.4	2.1	2.4	2.7	
			8 MHz	3.4	4.0	4.6	5.1	0.7	1.1	1.4	1.9	

1. Guaranteed by characterization results.
2. Data based on characterization results and tested in production with code executing from RAM.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 49. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/72 MHz	
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, LQFP64 package compliant with IEC 61967-2	0.1 to 30 MHz	5	dBµV
			30 to 130 MHz	6	
			130 MHz to 1GHz	28	
			SAE EMI Level	4	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

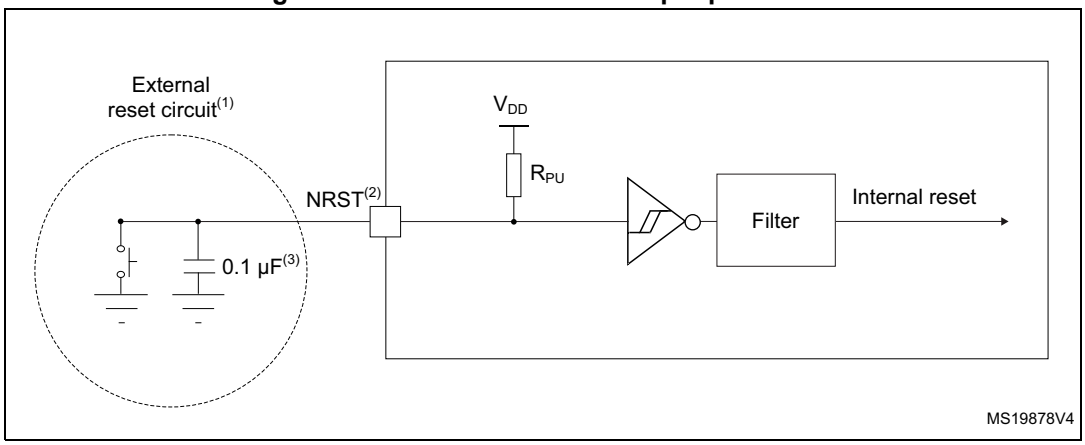
Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 50. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Packages	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114	All	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	LQFP64, WLCSP49	C3	250	V
			All other	C4	500	

1. Guaranteed by characterization results.

Figure 24. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 56*. Otherwise the reset will not be taken into account by the device.
3. The user must place the external capacitor on NRST as close as possible to the chip.

6.3.16 Timer characteristics

The parameters given in *Table 57* are guaranteed by design.

Refer to *Section 6.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 57. TIMx(1)(2) characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	13.9	-	ns
		$f_{TIMxCLK}$ = 144 MHz, x = 1, 15,16, 17	6.95	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 72 MHz	0	36	MHz
Res_{TIM}	Timer resolution	TIMx (except TIM2)	-	16	bit
		TIM2	-	32	
$t_{COUNTER}$	16-bit counter clock period	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	0.0139	910	µs
		$f_{TIMxCLK}$ = 144 MHz, x= 1/15/16/17	0.0069	455	µs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	-	59.65	s
		$f_{TIMxCLK}$ = 144 MHz, x= 1/15/16/17	-	29.825	s

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM15, TIM16 and TIM17 timers.
2. Guaranteed by design.

Table 58. IWDG min/max timeout period at 40 kHz (LSI) (1)

Prescaler divider	PR[2:0] bits	Min timeout (ms) RL[11:0]= 0x000	Max timeout (ms) RL[11:0]= 0xFFF
/4	0	0.1	409.6
/8	1	0.2	819.2
/16	2	0.4	1638.4
/32	3	0.8	3276.8
/64	4	1.6	6553.6
/128	5	3.2	13107.2
/256	7	6.4	26214.4

1. These timings are given for a 40 kHz clock but the microcontroller internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 59. WWDG min-max timeout value @72 MHz (PCLK)(1)

Prescaler	WDGTB	Min timeout value	Max timeout value
1	0	0.05687	3.6409
2	1	0.1137	7.2817
4	2	0.2275	14.564
8	3	0.4551	29.127

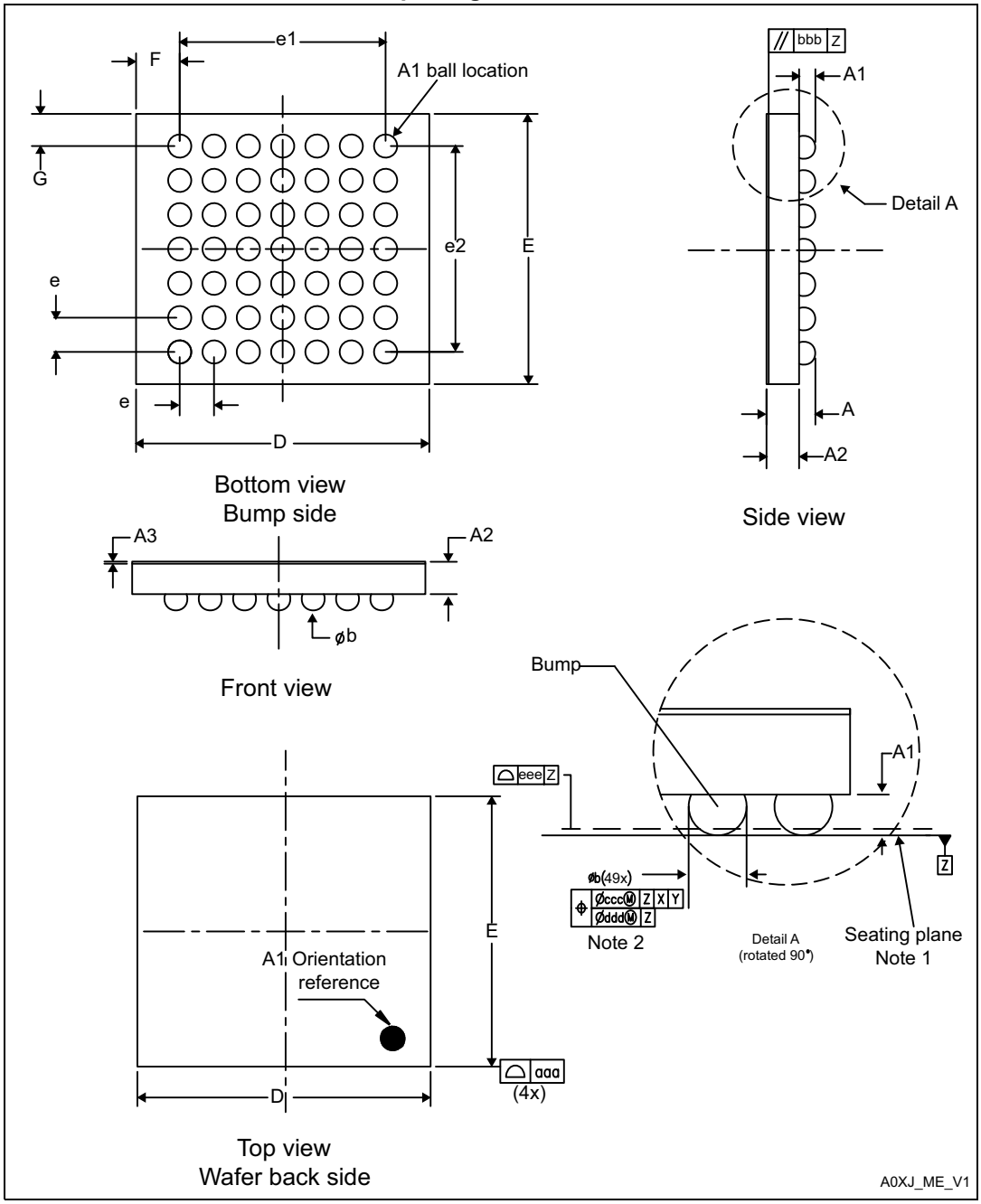
1. Guaranteed by design.

Table 69. ADC accuracy (1)(2)(3)

Symbol	Parameter	Conditions			Min(4)	Max (4)	Unit
ET	Total unadjusted error	ADC clock freq. ≤ 72 MHz, Sampling freq. ≤ 5 Msps 2.0 V ≤ V_{DDA} ≤ 3.6 V	Single ended	Fast channel 5.1 Ms	-	±6.5	LSB
				Slow channel 4.8 Ms	-	±6.5	
			Differential	Fast channel 5.1 Ms	-	±4	
				Slow channel 4.8 Ms	-	±4.5	
EO	Offset error		Single ended	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2.5	
				Slow channel 4.8 Ms	-	±2.5	
EG	Gain error		Single ended	Fast channel 5.1 Ms	-	±6	
				Slow channel 4.8 Ms	-	±6	
			Differential	Fast channel 5.1 Ms	-	±3.5	
				Slow channel 4.8 Ms	-	±4	
ED	Differential linearity error		Single ended	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
			Differential	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
EL	Integral linearity error		Single ended	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3.5	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2.5	
ENOB (5)	Effective number of bits		Single ended	Fast channel 5.1 Ms	10.4	-	bits
				Slow channel 4.8 Ms	10.4	-	
			Differential	Fast channel 5.1 Ms	10.8	-	
				Slow channel 4.8 Ms	10.8	-	
SINAD (5)	Signal-to-noise and distortion ratio		Single ended	Fast channel 5.1 Ms	64	-	dB
				Slow channel 4.8 Ms	63	-	
			Differential	Fast channel 5.1 Ms	67	-	
				Slow channel 4.8 Ms	67	-	

7.1 WLCSP49 package information

Figure 37. WLCSP49 - 49-pin, 3.417 x 3.151 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

Table 77. WLCSP49 - 49-pin, 3.417 x 3.151 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	3.382	3.417	3.452	0.1331	0.1345	0.1359
E	3.116	3.151	3.186	0.1227	0.1241	0.1254
e	-	0.400	-	-	0.0157	-
e1	-	2.400	-	-	0.0945	-
e2	-	2.400	-	-	0.0945	-
F	-	0.5085	-	-	0.0200	-
G	-	0.3755	-	-	0.0148	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 38. WLCSP49 - 49-pin, 3.417 x 3.151 mm, 0.4 mm pitch wafer level chip scale package recommended footprint

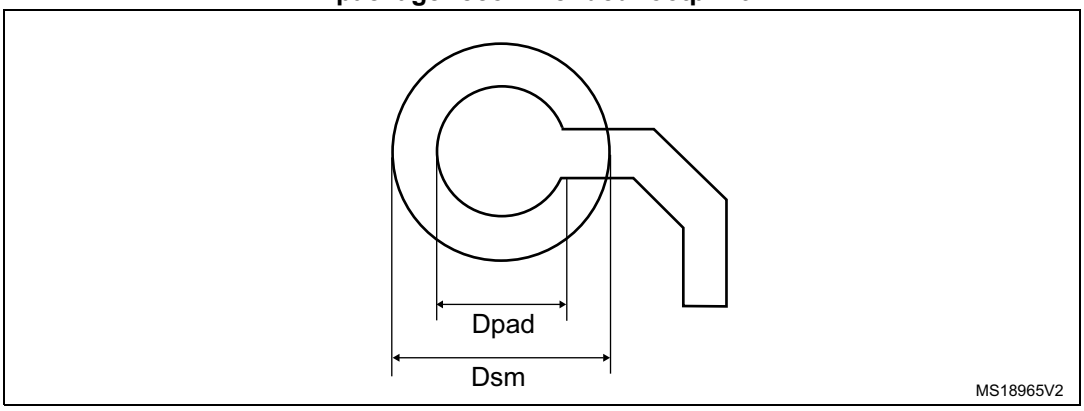
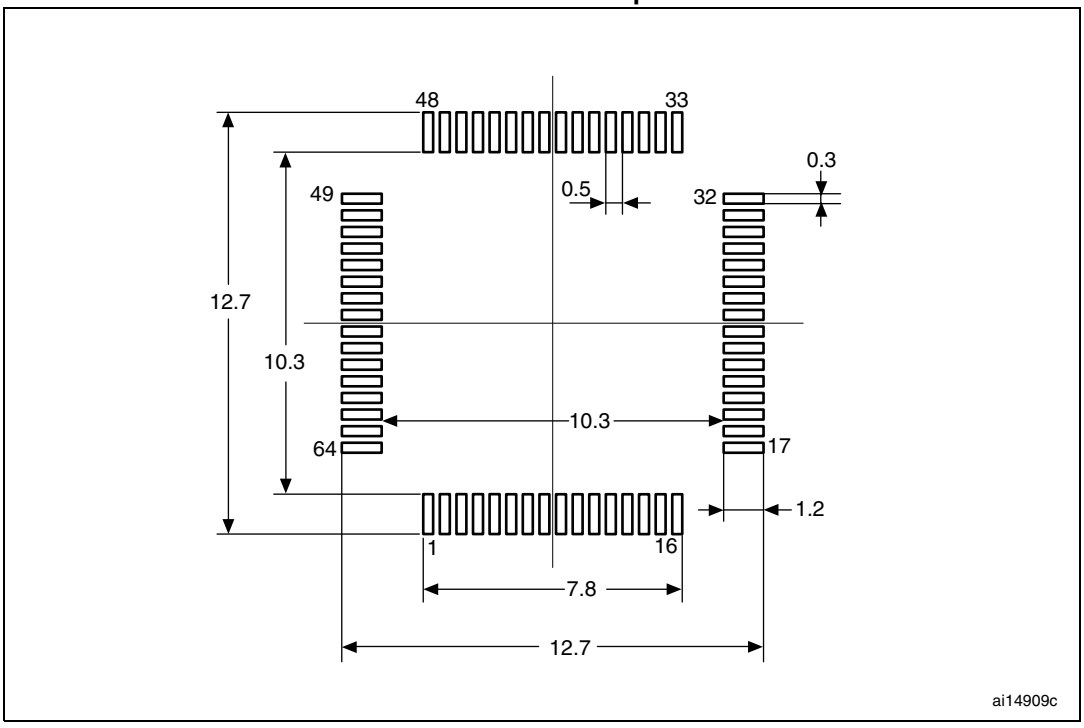


Table 79. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

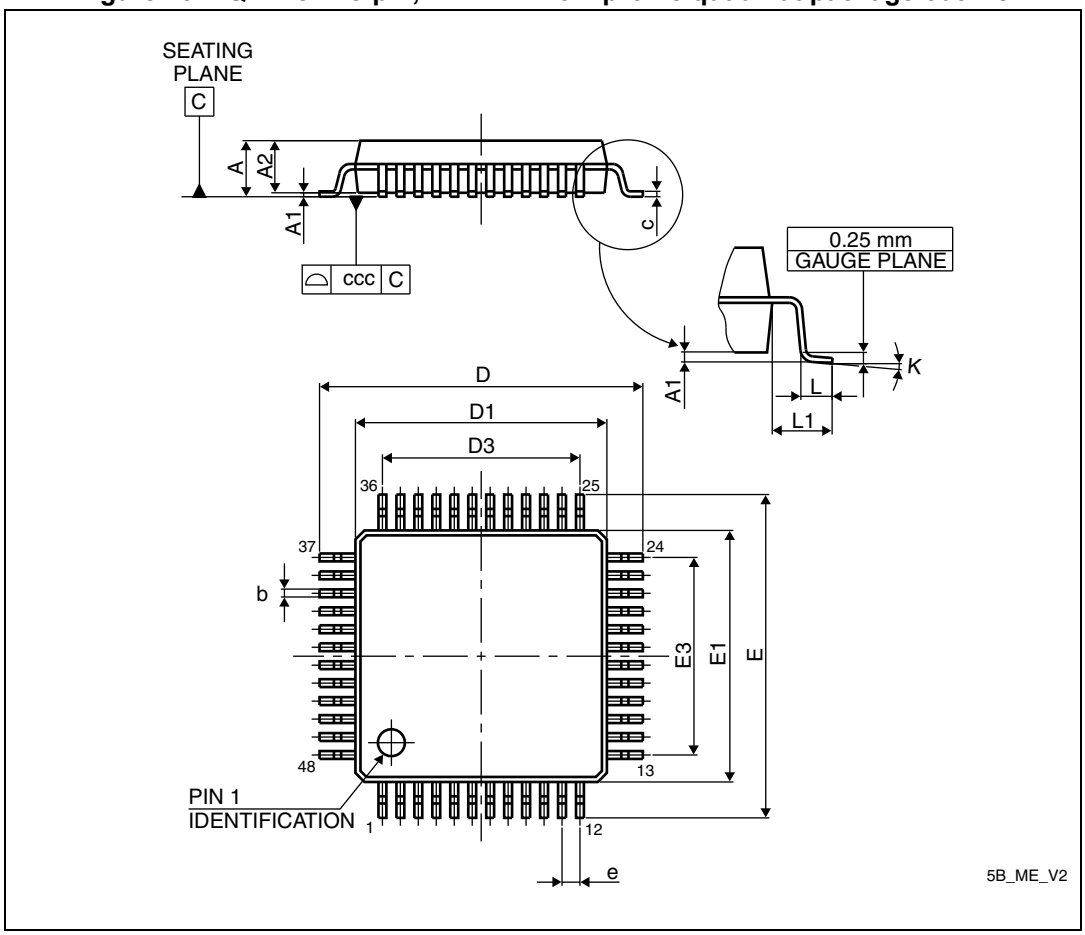
Figure 41. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

7.3 LQFP48 package information

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 80. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 115 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 9 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 9 × 8 mA × 0.4 V = 28.8 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 28.8 mW:

P_{Dmax} = 70 + 28.8 = 98.8 mW

Thus: P_{Dmax} = 98.8 mW

Using the values obtained in *Table 82* T_{Jmax} is calculated as follows:

– For LQFP100, 45°C/W

T_{Jmax} = 115°C + (45°C/W × 98.8 mW) = 115 °C + 4.44°C = 119.44°C

This is within the range of the suffix 7 version parts (–40 < T_J < 125 °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Section 8: Ordering information*).